Attorney Docket: 013921-000025

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Linthicum, Kevin J.

Serial Number: Unassigned

Related Application Info:
Ser. No. 09/850,687
Filed: May 7, 2001

Filed: Concurrently Herewith

For: PENDEOEPITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS ON SILICON WAFERS OR WAFERS CONTAINING SILICON, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. § 1.56 AND 37 C.F.R. § 1.97

It is respectfully requested that the document(s) listed on the attached Form PTO/1449 be considered by the Patent and Trademark Office in the above-referenced application and made of record therein. All items listed on the PTO/1449 were cited in parent application Serial No. 09/850,687, filed November 24, 1998. Since the benefit of this application is claimed under 35 U.S.C. §120, no copies need to be furnished in accordance with 37 C.F.R. §1.98(d); however, copies will be furnished on request.

Respectfully submitted,

By: _____

Steven B. Phillips
Registration No. 37,911
Attorney for Applicant
Moore & Van Allen, PLLC
2200 West Main Street, Suite 800
Durham, NC 27705
Phone: 919-286-8000
Facsimile: 919-286-8199

August 4, 2003
Date

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the US Postal Service as first class mail on August 4, 2003, in an envelope addressed to Commissioner of Patents, PO Box 1450, Alexandria, VA 22313-1450

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Patricia L. Pontello

Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 5051-448CT	Serial No.: To Be Assigned
	Applicants: Kevin J. Linthicum, et al.	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Filing Date: Concurrently Herewith	GAU:

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